The RF Line Microwave Pulse Power Transistors

Designed for Class B and C common base amplifier applications in short and long pulse TACAN, IFF, DME, and radar transmitters.

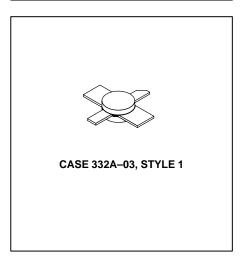
- Guaranteed Performance @ 1090 MHz, 50 Vdc Output Power = 35 Watts Peak Minimum Gain = 10 dB
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- · Industry Standard Package
- Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input Matching for Broadband Operation

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|------------------|-------------|----------------|
| Collector-Emitter Voltage | V _{CES} | 60 | Vdc |
| Collector-Base Voltage | V _{CBO} | 60 | Vdc |
| Emitter-Base Voltage | VEBO | 4.0 | Vdc |
| Collector-Current — Continuous | IC | 2.0 | Adc |
| Total Device Dissipation @ T _C = 25°C (1) Derate above 25°C | PD | 35 200 | Watts mW/°C |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |

MRF1035MB

35 W (PEAK), 960-1215 MHz MICROWAVE POWER TRANSISTORS NPN SILICON



THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|----------------|-----|------|
| Thermal Resistance, Junction to Case (2) | $R_{	heta JC}$ | 5.0 | °C/W |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|----------|-----|-----|-----|------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Emitter Breakdown Voltage (IC = 20 mAdc, VBE = 0) | V(BR)CES | 60 | _ | _ | Vdc |
| Collector-Base Breakdown Voltage (I _C = 20 mAdc, I _E = 0) | V(BR)CBO | 60 | _ | _ | Vdc |
| Emitter-Base Breakdown Voltage (I _E = 2.0 mAdc, I _C = 0) | V(BR)EBO | 4.0 | _ | _ | Vdc |
| Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0) | ICBO | _ | _ | 2.0 | mAdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (IC = 500 mAdc, VCE = 5.0 Vdc) | hFE | 10 | 40 | 100 | _ |

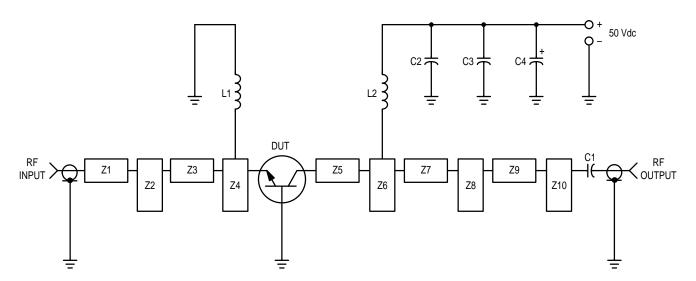
^{1.} These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.



^{2.} Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

ELECTRICAL CHARACTERISTICS — **continued** ($T_C = 25$ °C unless otherwise noted.)

| Characteristic | Symbol | Min | Тур | Max | Unit | |
|--|-----------------|--------------------------------|------|-----|------|--|
| DYNAMIC CHARACTERISTICS | | | | | | |
| Output Capacitance (V _{CB} = 50 Vdc, I _E = 0, f = 1.0 MHz) | C _{ob} | _ | 10 | 15 | pF | |
| FUNCTIONAL TESTS (Pulse Width = 10 μs, Duty Cycle = 1%) | | | | | | |
| Common-Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{Out} = 35 W Peak, f = 1090 MHz) | GPB | 10 | 12.4 | _ | dB | |
| Collector Efficiency (V _{CC} = 50 Vdc, P _{Out} = 35 W Peak, f = 1090 MHz) | η | 30 | 34 | _ | % | |
| Load Mismatch (V _{CC} = 50 Vdc, P _{Out} = 35 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles) | Ψ | No Degradation in Power Output | | | | |



C1, C2 — 220 pF 100 mil Chip Capacitor C3 — 0.1 μ F C4 — 10 μ F/75 V Electrolytic L1, L2 — 3 Turns #18 AWG, 1/8" ID Z1–Z10 — Microstrip, See Photomaster Board Material — 0.031" Glass Teflon ϵ_Γ = 2.5

Figure 1. 1090 MHz Test Circuit

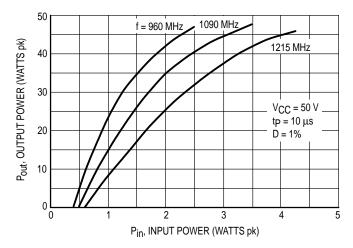


Figure 2. Output Power versus Input Power

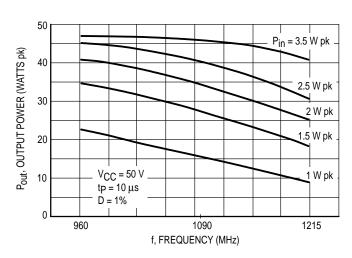


Figure 3. Output Power versus Frequency

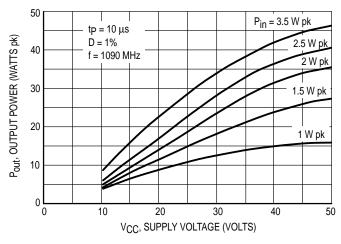


Figure 4. Output Power versus Supply Voltage

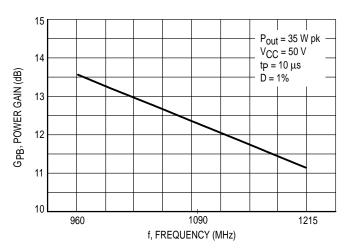
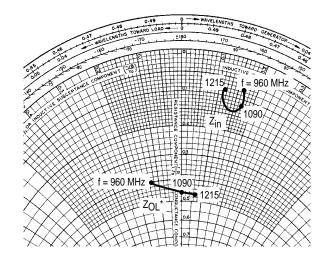


Figure 5. Power Gain versus Frequency



 $P_{out} = 35 \text{ W pk}$ $V_{CC} = 50 \text{ V}$ $t_p = 10 \text{ µs}$ D = 1%

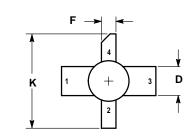
| f | Z _{in} | Z _{OL} * |
|------|-----------------|-------------------|
| MHz | Ohms | Ohms |
| 960 | 3.8 + j8.2 | 7.5 – j3.3 |
| 1090 | 6.0 + j8.2 | 9.0 + j0 |
| 1215 | 4.2 + j5.7 | 9.1 + i1.7 |

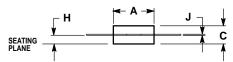
Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.

Figure 6. Series Equivalent Input/Output Impedances

MOTOROLA RF DEVICE DATA MRF1035MB

PACKAGE DIMENSIONS





- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.270 | 0.290 | 6.86 | 7.36 |
| C | 0.115 | 0.135 | 2.93 | 3.42 |
| D | 0.195 | 0.205 | 4.96 | 5.20 |
| F | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.050 | 0.070 | 1.27 | 1.77 |
| 7 | 0.003 | 0.007 | 0.08 | 0.17 |
| К | 0.600 | | 15 24 | |

STYLE 1:

PIN 1. BASE 2. EMITTER

- 3. BASE 4. COLLECTOR

CASE 332A-03 ISSUE D

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